

isc N-Channel MOSFET Transistor

2SK2905-01R

FEATURES

- Drain Current : I_D= 70A@ T_C=25 ℃
- Drain Source Voltage
 - : V_{DSS}= 60V(Min)
- Static Drain-Source On-Resistance
 - : $R_{DS(on)} = 12m \Omega (Max)$
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRIPTION

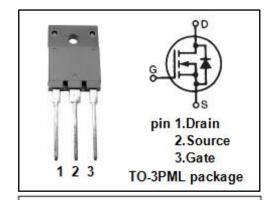
 motor drive, DC-DC converter, power switch and solenoid drive.

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage	60	V
V _{GS}	Gate-Source Voltage-Continuous	±20	V
I _D	Drain Current-Continuous	70	А
I _{DM}	Drain Current-Single Pluse	280	А
P _D	Total Dissipation @Tc=25℃	100	W
TJ	Max. Operating Junction Temperature	-55~150	$^{\circ}$
T _{stg}	Storage Temperature	-55~150	$^{\circ}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	1.25	°C/W



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	R	÷J .	N - D
<u> </u>	m		N D
DIM	m MIN	MAX	N D
Α	MIN 19.90	MAX 20.10	N D
A B	MIN 19.90 15.75	MAX 20.10 16.10	N D
A B C	MIN 19.90 15.75 5.50	MAX 20.10 16.10 5.70	N D
A B C D	MIN 19.90 15.75 5.50 0.90	MAX 20.10 16.10 5.70 1.10	N D
A B C D	MIN 19.90 15.75 5.50 0.90 3.30	MAX 20.10 16.10 5.70 1.10 3.50	N D
A B C D F	MIN 19.90 15.75 5.50 0.90 3.30 2.90	MAX 20.10 16.10 5.70 1.10 3.50 3.20	N D
A B C D F G	MIN 19.90 15.75 5.50 0.90 3.30 2.90 5.90	MAX 20.10 16.10 5.70 1.10 3.50 3.20 6.10	N D
A B C D F	MIN 19.90 15.75 5.50 0.90 3.30 2.90	MAX 20.10 16.10 5.70 1.10 3.50 3.20	N D

D	0.90	1.10
F	3.30	3.50
G	2.90	3.20
Н	5.90	6.10
J	0.595	0.70
K	21.10	22.50
L	1.90	2.25
N	10.80	11.00
0	4.90	5.10
R	3.75	3.95
S	3.20	3.60
U	9.90	10.10
Y	4.20	4.90
Z	1.90	2.10

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ELECTRICAL CHARACTERISTICS

T_c=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = 1mA	60		V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = 10V; I _D = 1mA	2.5	3.5	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D = 40A		12	m Ω
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V;V _{DS} = 0		±0.1	uA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 60V; V _{GS} = 0		500	uA
V _{SD}	Forward On-Voltage	I _S = 50A; V _{GS} = 0	-	1.5	V

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